Supplementary Information.

Chemical gating of epitaxial graphene through ultrathin oxide layers

Rosanna Larciprete,¹ Paolo Lacovig,² Fabrizio Orlando,³,⁴ Matteo Dalmiglio,² Luca Omiciuolo,³ Alessandro Baraldi,²,³,⁵ and Silvano Lizzit²

¹CNR-Institute for Complex Systems,

Via Fosso del Cavaliere 100, 00133 Roma, Italy

²Elettra Sincrotrone Trieste S.C.p.A., AREA Science Park,

 $S.S.\ 14\ Km\ 163.5,\ 34149\ Basovizza,\ Italy$

³Physics Department, University of Trieste,

Via Valerio 2, 34127 Trieste, Italy

⁴present address Laboratory of Radiochemistry and Environmental Chemistry,

Paul Scherrer Institut, 5232 Villigen PSI, Switzerland

⁵IOM-CNR Laboratorio TASC, Area Science Park,

 $S.S.14\ Km\ 163.5,\ 34149\ Trieste,\ Italy$

I. NEXAFS SPECTROSCOPY

The C K-edge NEXAFS spectra were measured in the Auger yield mode by revealing the photoelectrons at a kinetic energy of 260 eV corresponding to the C-KLL transition. Angular dependent spectra were taken as a function of the angle θ between the electric field E of the photon beam (which was horizontally polarized) and the normal to the substrate plane (or between the x-ray beam and the substrate plane). The angle θ was varied between 20° (grazing incidence) and 90° (normal incidence) by rotating the samples. The strong dichroism between the spectra measured in the two geometries observed for all interfaces indicate that graphene remains flat on the substrate plane.

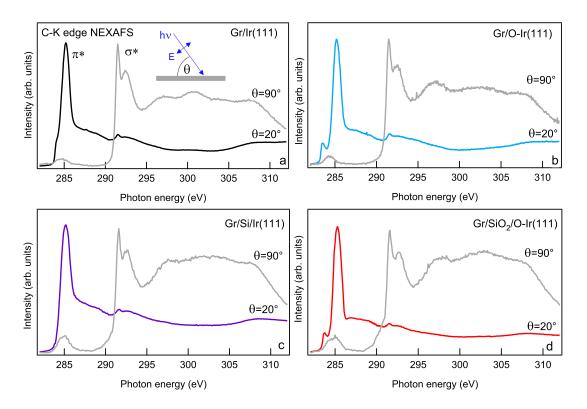


FIG. 1. Angular dependence of the NEXAFS spectra measured (a) on the Gr/Ir(111) surface, after the intercalation of (b) oxygen (0.5 ML) or (c) silicon (2.6 ML), and (d) after the synthesis or SiO_2 (3.5 ML) by stepwise intercalation of Si and O. The NEXAFS spectra were aligned at the position of the σ^* resonance at 291.5 eV.